

# **RB520S30**

# 200 mA low V<sub>F</sub> MEGA Schottky barrier rectifier Rev. 01 — 6 October 2009

**Product data sheet** 

## **Product profile**

#### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD523 (SC-79) ultra small and flat lead Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features

Average forward current: I<sub>F(AV)</sub> ≤ 0.2 A

Reverse voltage: V<sub>R</sub> ≤ 30 V

■ Low reverse current:  $I_R \le 1 \mu A$ 

AEC-Q101 qualified

Ultra small and flat lead SMD plastic package

## 1.3 Applications

- Low current rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

#### 1.4 Quick reference data

Table 1. **Quick reference data**  $T_i = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	square wave; $\delta = 0.5$ ; $f = 20 \text{ kHz}$				
		T <sub>amb</sub> ≤ 105 °C	<u>[1]</u> _	-	0.2	Α
		T <sub>sp</sub> ≤ 135 °C	-	-	0.2	Α
I <sub>R</sub>	reverse current	$V_R = 10 V$	-	-	1	μΑ
$V_R$	reverse voltage		-	-	30	V
$V_{F}$	forward voltage	$I_F = 0.2 A$	[2]	520	600	mV

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, mounting pad for cathode 1 cm<sup>2</sup>.



<sup>[2]</sup> Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .

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# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	<u>[1]</u>	
2	anode		1 - 2
			sym001

<sup>[1]</sup> The marking bar indicates the cathode.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
RB520S30	SC-79	plastic surface-mounted package; 2 leads	SOD523

# 4. Marking

Table 4. Marking codes

Type number	Marking code
RB520S30	ZA

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	reverse voltage	$T_j = 25  ^{\circ}C$	-	30	V
I <sub>F(AV)</sub>	average forward current	square wave; $\delta$ = 0.5; f = 20 kHz			
		T <sub>amb</sub> ≤ 105 °C	<u>[1]</u> _	0.2	Α
		T <sub>sp</sub> ≤ 135 °C	-	0.2	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 8.3 ms half sine wave; JEDEC method	[2] -	1	A
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[3][4]	275	mW
			[3][1]	420	mW
			[3][5]	500	mW

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 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$T_j$	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [2]  $T_i = 25$  °C prior to surge.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

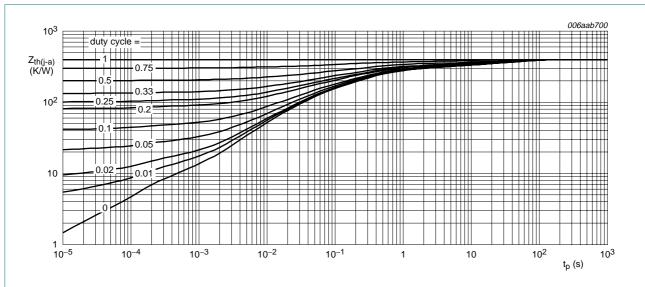
#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance from	in free air	[1][2]			
		[3]	-	455	K/W	
			<u>[4]</u> _	-	300	K/W
			[5] _	-	250	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[6] _	-	90	K/W

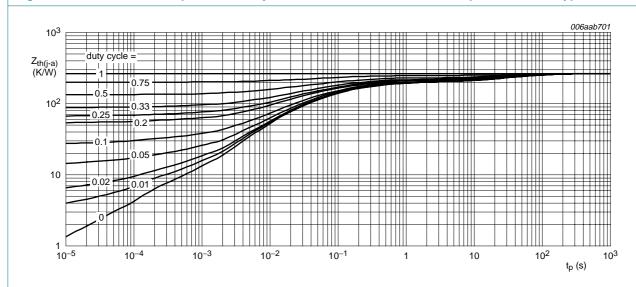
- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [6] Soldering point of cathode tab.

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FR4 PCB, standard footprint

Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 200 mA low V<sub>F</sub> MEGA Schottky barrier rectifier

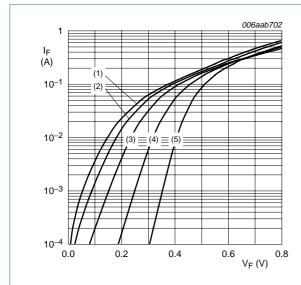
# 7. Characteristics

Table 7. Characteristics

 $T_i = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage		[1]			
		$I_F = 0.1 \text{ mA}$	-	190	220	mV
		$I_F = 1 \text{ mA}$	-	250	290	mV
	$I_F = 10 \text{ mA}$	-	320	360	mV	
	$I_F = 100 \text{ mA}$	-	440	500	mV	
		$I_F = 200 \text{ mA}$	-	520	600	mV
$I_R$	reverse current	V <sub>R</sub> = 10 V	-	-	1	μΑ
C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 1 V$	-	-	20	pF

[1] Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 





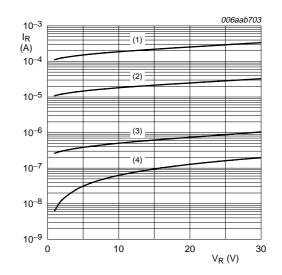
(2) 
$$T_j = 125 \,^{\circ}\text{C}$$

(3) 
$$T_i = 85 \, ^{\circ}C$$

(4) 
$$T_j = 25 \,^{\circ}C$$

(5) 
$$T_j = -40 \, ^{\circ}C$$

Fig 3. Forward current as a function of forward voltage; typical values



(1)  $T_j = 125 \, ^{\circ}C$ 

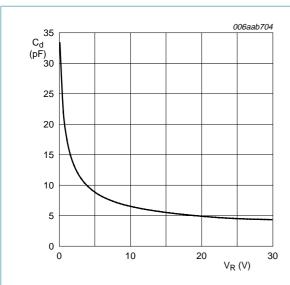
(2) 
$$T_i = 85 \,^{\circ}\text{C}$$

(3) 
$$T_i = 25 \,^{\circ}C$$

(4) 
$$T_j = -40 \, ^{\circ}C$$

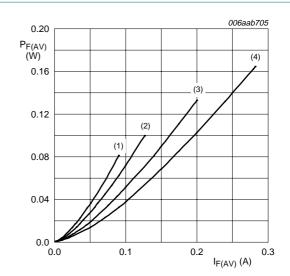
Fig 4. Reverse current as a function of reverse voltage; typical values

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 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ 

Fig 5. Diode capacitance as a function of reverse voltage; typical values



T<sub>j</sub> = 150 °C

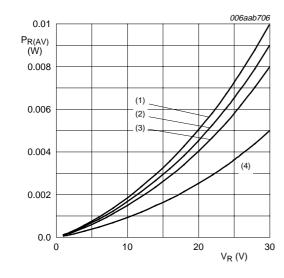
(1)  $\delta = 0.1$ 

(2)  $\delta = 0.2$ 

(3)  $\delta = 0.5$ 

(4)  $\delta = 1$ 

Fig 6. Average forward power dissipation as a function of average forward current; typical values



T<sub>i</sub> = 125 °C

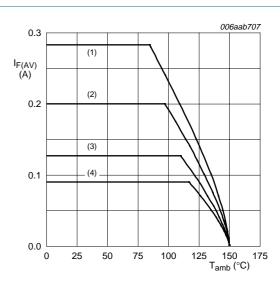
(1)  $\delta = 1$ 

(2)  $\delta = 0.9$ 

(3)  $\delta = 0.8$ 

(4)  $\delta = 0.5$ 

Fig 7. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T<sub>i</sub> = 150 °C

(1)  $\delta = 1$ ; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

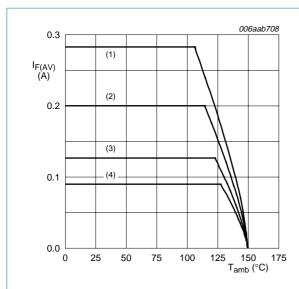
(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 8. Average forward current as a function of ambient temperature; typical values

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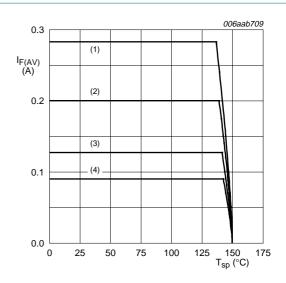
#### 200 mA low V<sub>F</sub> MEGA Schottky barrier rectifier



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

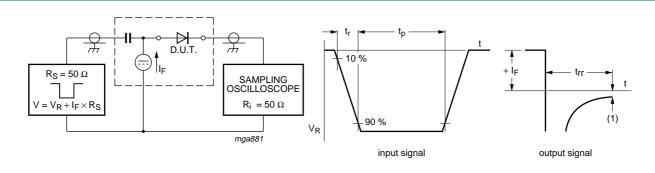
Fig 9. Average forward current as a function of ambient temperature; typical values



- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

Fig 10. Average forward current as a function of solder point temperature; typical values

## 8. Test information



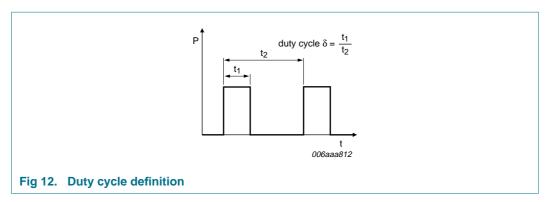
(1)  $I_R = 1 \text{ mA}$ 

Input signal: reverse pulse rise time  $t_r$  = 0.6 ns; reverse voltage pulse duration  $t_p$  = 100 ns; duty cycle  $\delta$  = 0.05 Oscilloscope: rise time  $t_r$  = 0.35 ns

Fig 11. Reverse recovery time test circuit and waveforms

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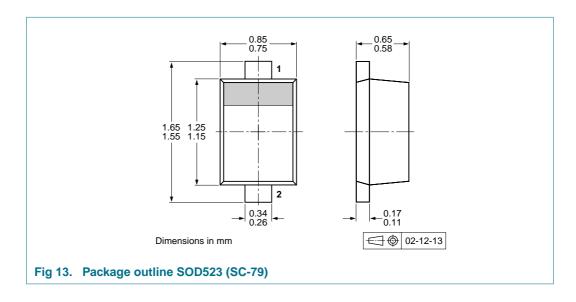


The current ratings for the typical waveforms as shown in Figure 8, 9 and 10 are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



#### 200 mA low V<sub>F</sub> MEGA Schottky barrier rectifier

# 10. Packing information

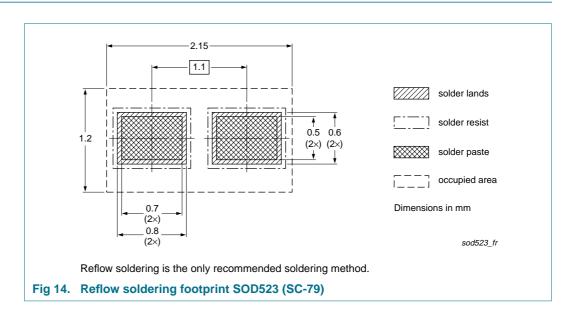
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packin	g quanti	ty
			3000	8000	10000
RB520S30	SOD523	2 mm pitch, 8 mm tape and reel	-	-315	-
		4 mm pitch, 8 mm tape and reel	-115	-	-135

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

# 11. Soldering



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# 12. Revision history

## Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
RB520S30_1	20091006	Product data sheet	-	-

#### 200 mA low V<sub>F</sub> MEGA Schottky barrier rectifier

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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